

DISCRETE SEMICONDUCTORS

DATA SHEET

PMBTH81

PNP 1 GHz switching transistor

Product specification

September 1995

File under Discrete Semiconductors, SC14

PNP 1 GHz switching transistor

PMBTH81

FEATURES

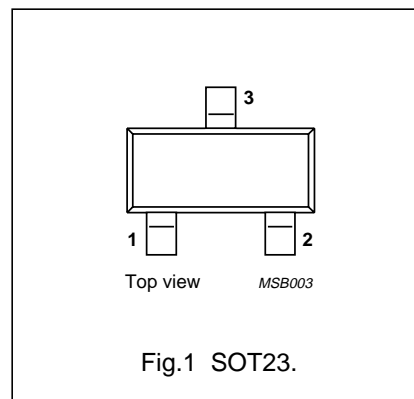
- Low cost
- High transition frequency.

DESCRIPTION

The PMBTH81 is a general purpose silicon pnp transistor, encapsulated in a SOT23 plastic envelope. Its complement is the PMBTH10.

PINNING

PIN	DESCRIPTION
Code: V31	
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	20	V
P_{tot}	total power dissipation	$T_s = 45\text{ °C}$ (note 1)	–	400	mW
C_{ce}	collector-emitter capacitance	$V_{CB} = 10\text{ V}$; $I_B = 0$; $f = 1\text{ MHz}$	–	0.65	pF
C_{cb}	collector-base capacitance	$V_{CB} = 10\text{ V}$; $I_E = 0$; $f = 1\text{ MHz}$	–	0.85	pF
f_T	transition frequency	$V_{CE} = 10\text{ V}$; $I_C = 5\text{ mA}$; $f = 100\text{ MHz}$; $T_{amb} = 25\text{ °C}$	600	–	MHz

Note

1. T_s is the temperature at the soldering point of the collector tab.

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	20	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current		–	40	mA
P_{tot}	total power dissipation	$T_s = 45\text{ °C}$ (note 1)	–	400	mW
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	150	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	THERMAL RESISTANCE
$R_{th\ j-s}$	from junction to soldering point (note 1)	260 K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

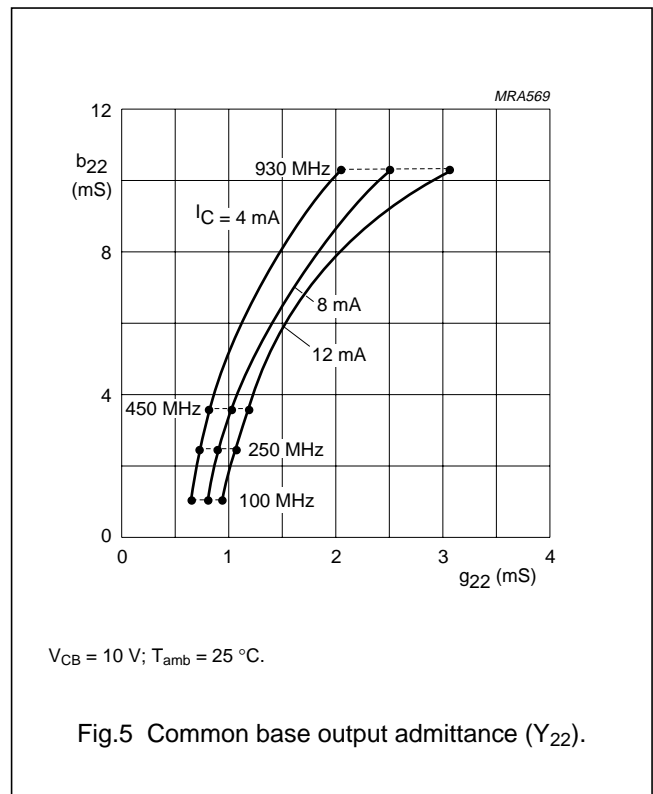
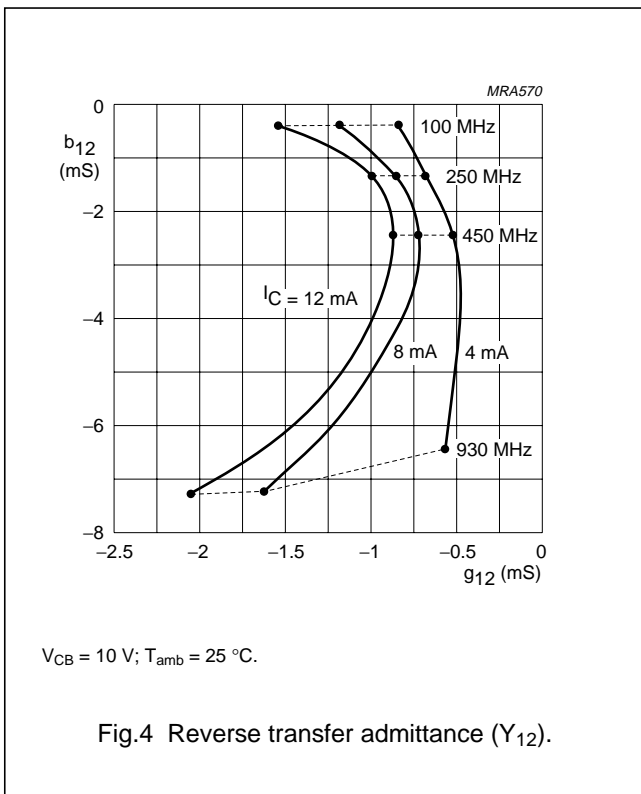
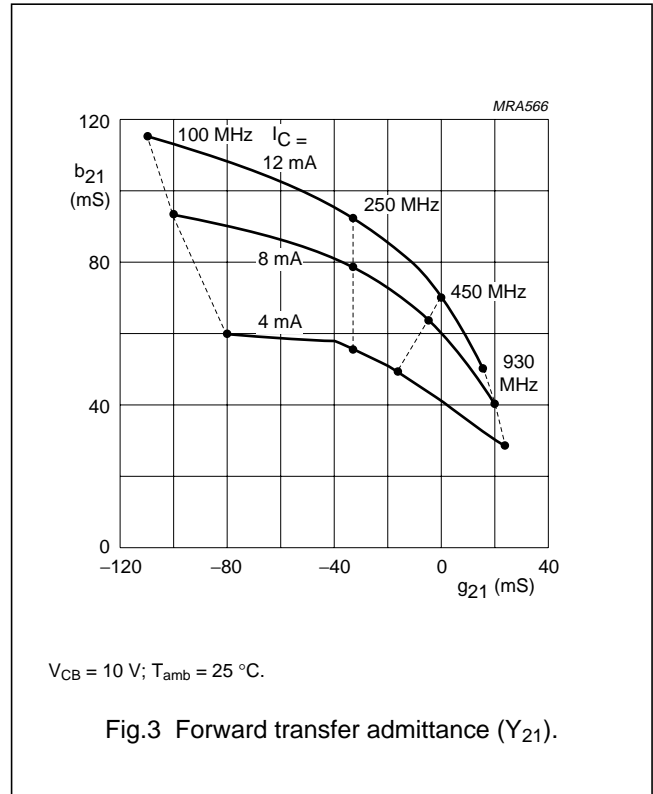
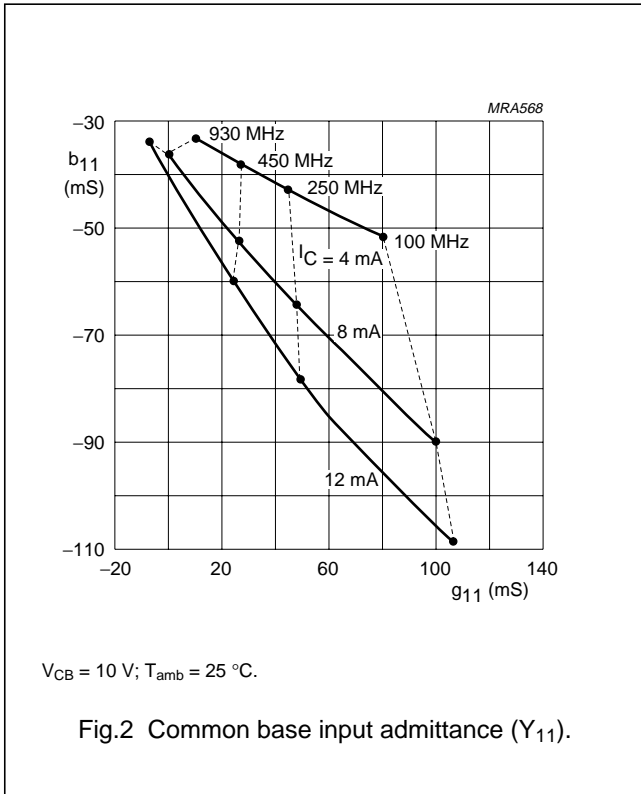
CHARACTERISTICS

$T_j = 25\text{ °C}$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 10\ \mu\text{A}$; $I_E = 0$	20	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = 1\ \text{mA}$; $I_B = 0$	20	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = 10\ \mu\text{A}$; $I_C = 0$	3	–	V
$V_{CE\ sat}$	collector-emitter saturation voltage	$I_C = 5\ \text{mA}$; $I_B = 0.5\ \text{mA}$	–	0.5	V
$V_{BE\ on}$	base-emitter ON voltage	$V_{CE} = 10\ \text{V}$; $I_C = 5\ \text{mA}$	–	0.9	V
I_{CBO}	collector-base cut-off current	$V_{CB} = 10\ \text{V}$; $I_E = 0$	–	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 2\ \text{V}$; $I_C = 0$	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 10\ \text{V}$; $I_C = 5\ \text{mA}$	60	–	
C_{ce}	collector-emitter capacitance	$V_{CB} = 10\ \text{V}$; $I_B = 0$; $f = 1\ \text{MHz}$	–	0.65	pF
C_{cb}	collector-base capacitance	$V_{CB} = 10\ \text{V}$; $I_E = 0$; $f = 1\ \text{MHz}$	–	0.85	pF
f_T	transition frequency	$V_{CE} = 10\ \text{V}$; $I_C = 5\ \text{mA}$; $f = 100\ \text{MHz}$; $T_{amb} = 25\text{ °C}$	600	–	MHz

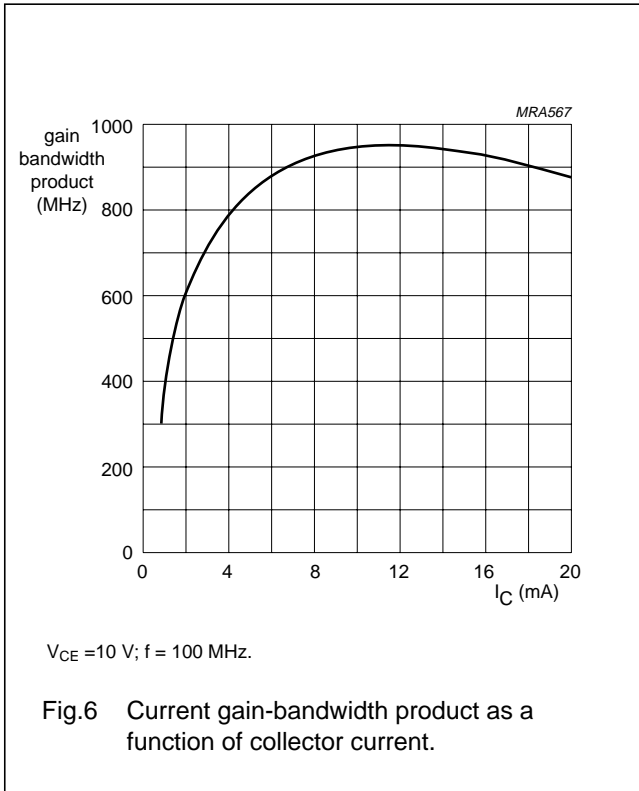
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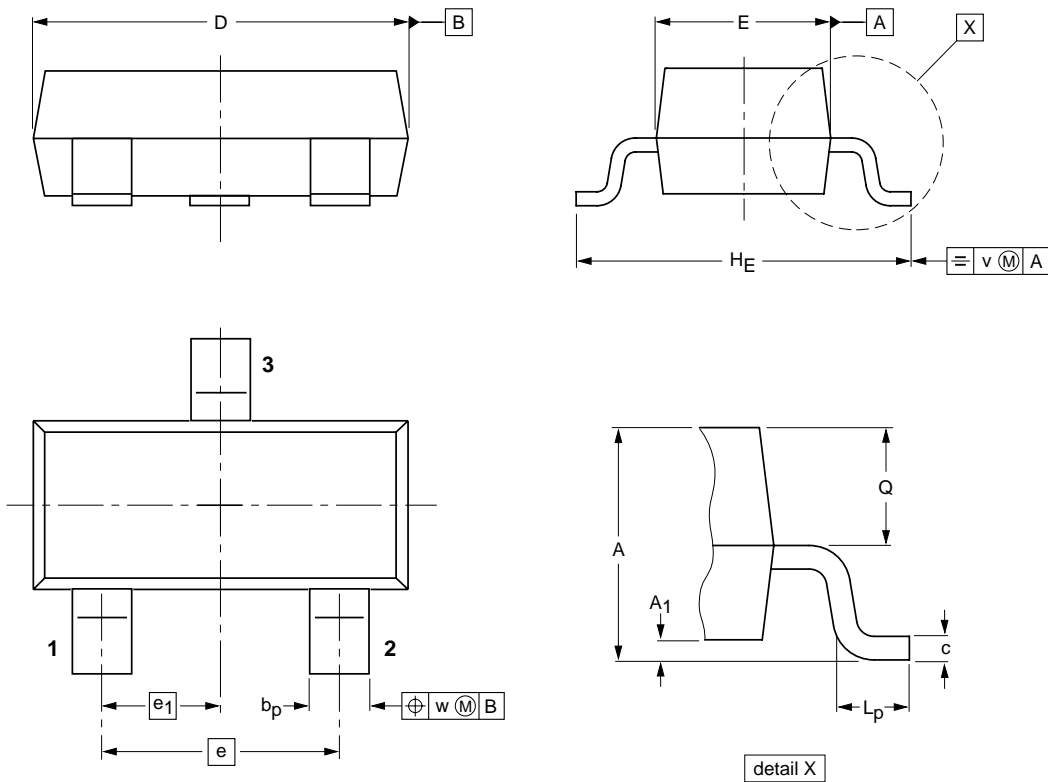
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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